

PHEMT GaAs IC High Linearity Positive Control SPDT Switch DC–2 GHz



AS178-73

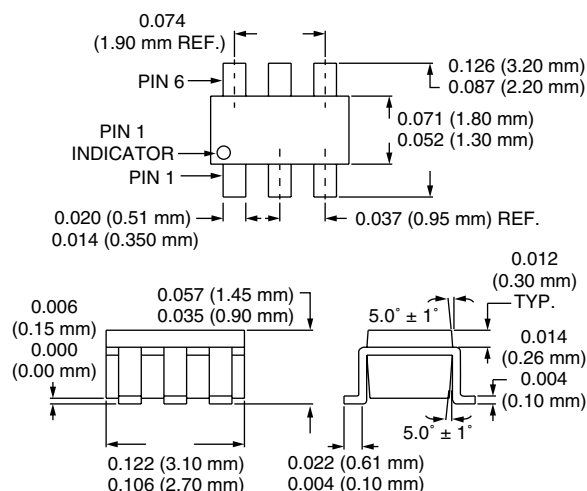
Features

- High Linearity (50 dBm IP3 @ 0.9 GHz)
@ 3 V
- Low Insertion Loss (0.35 dB @ 0.9 GHz)
- Isolation (21 dB @ 0.9 GHz)
- +3 V Operation
- Ultra Miniature SOT-6 Package
- PHEMT Process

Description

The AS178-73 is a PHEMT GaAs FET IC high linearity SPDT switch in a SOT-6 plastic package. This switch has been designed for use where extremely high linearity, low insertion loss and ultra miniature package size are required. It can be controlled with positive, negative or a combination of both voltages. Some standard implementations include antenna changeover, T/R and

SOT-6



diversity switching over 2 W. The AS178-73 switch can be used in many analog and digital wireless communication systems including cellular, GSM and DECT applications.

Electrical Specifications at 25°C (0, +3 V)

Parameter ¹	Frequency ²	Min.	Typ.	Max.	Unit
Insertion Loss ³	DC–0.5 GHz		0.45	0.6	dB
	DC–1.0 GHz		0.45	0.6	dB
	DC–2.0 GHz		0.55	0.7	dB
Isolation	DC–0.5 GHz	25	28		dB
	DC–1.0 GHz	20	23		dB
	DC–2.0 GHz	14	17		dB
VSWR ⁴	DC–1.0 GHz		1.2:1	1.4:1	
	DC–2.0 GHz		1.3:1	1.8:1	

Operating Characteristics at 25°C (0, +3 V)

Parameter	Condition	Frequency	Min.	Typ.	Max.	Unit
Switching Characteristics ⁵	Rise, Fall (10/90% or 90/10% RF)			60		ns
	On, Off (50% CTL to 90/10% RF)			100		ns
	Video Feedthru			50		mV
Input Power for 1 dB Compression	0/+3 V	0.9 GHz		+34		dBm
	0/+5 V	0.9 GHz		+38		dBm
Intermodulation Intercept Point (IP3)	For Two-tone Input Power +17 dBm					
	0/+3 V	0.9 GHz		+50		dBm
	0/+5 V	0.9 GHz		+57		dBm
Control Voltages	$V_{Low} = 0 \text{ to } 0.2 \text{ V @ } 20 \mu\text{A Max.}$ $V_{High} = +3 \text{ V @ } 100 \mu\text{A Max. to } +5 \text{ V @ } 200 \mu\text{A Max.}$ $V_S = V_{High} \pm 0.2 \text{ V}$					

1. All measurements made in a 50 Ω system, unless otherwise specified.

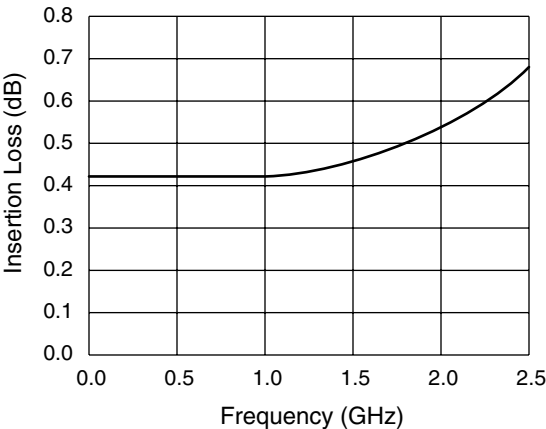
2. DC = 300 kHz.

3. Insertion loss changes by 0.003 dB/°C.

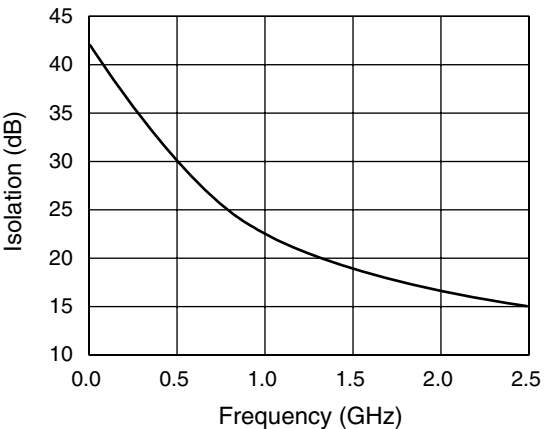
4. Insertion loss state.

5. Video feedthru measured with 1 ns risetime pulse and 500 MHz bandwidth.

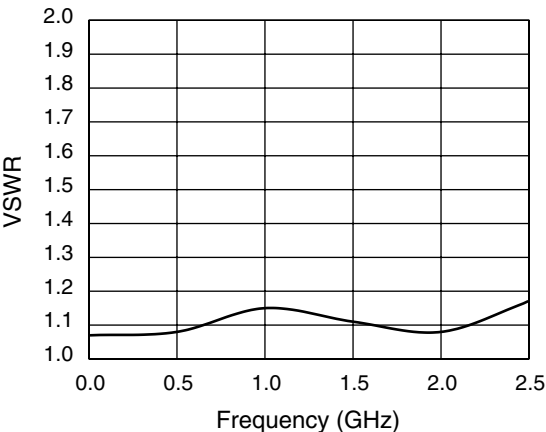
Typical Performance Data (0, +3 V)



Insertion Loss vs. Frequency



Isolation vs. Frequency



VSWR vs. Frequency

Truth Table

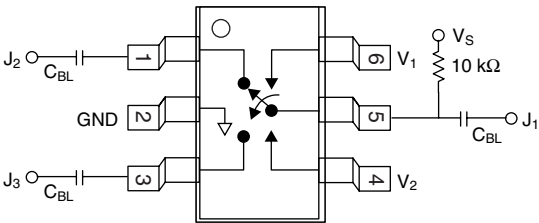
V ₁	V ₂	J ₁ –J ₂	J ₁ –J ₃
0	V _{High}	Isolation	Insertion Loss
V _{High}	0	Insertion Loss	Isolation

V_{High} = +3 to +5 V (V_S = V_{High} ± 0.2 V).

Absolute Maximum Ratings

Characteristic	Value
RF Input Power	10 W Max. > 900 MHz 0/+7 V Control
Control Voltage	-0.2 V, +8 V
Operating Temperature	-40°C to +85°C
Storage Temperature	-65°C to +150°C
Θ _{JC}	25°C/W

Pin Out



DC blocking capacitors (C_{BL}) must be supplied externally.
C_{BL} = 100 pF for operating frequency >500 MHz.